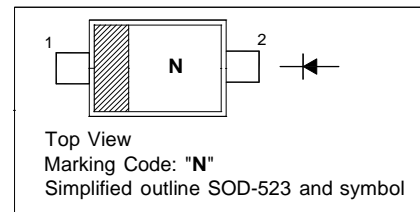


## Silicon Epitaxial Schottky Barrier Diode

for high speed switching application

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

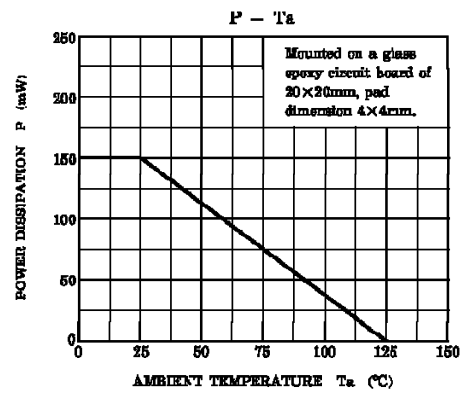
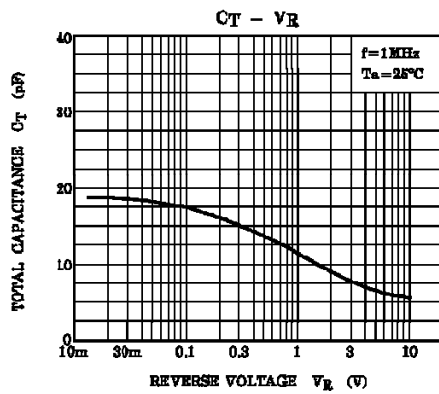
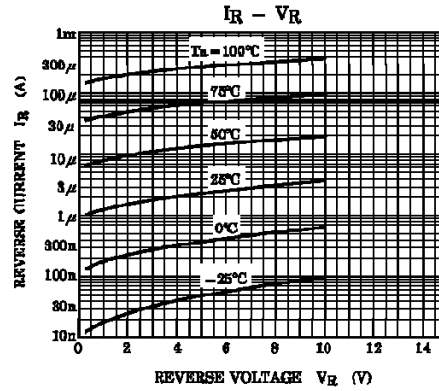
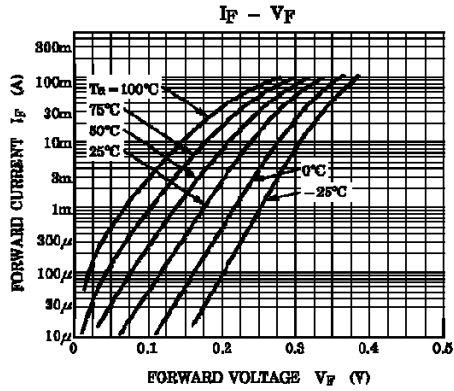


### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	$V_{RM}$	15	V
Reverse Voltage	$V_R$	10	V
Average Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	$I_{FM}$	200	mA
Surge Current (10 ms)	$I_{FSM}$	1	A
Power Dissipation	$P_{tot}$	150	mW
Operating Temperature Range	$T_{opr}$	- 40 to + 100	$^\circ\text{C}$
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 100\text{ mA}$	$V_F$	0.3 0.5	V
Reverse Current at $V_R = 10\text{ V}$	$I_R$	20	$\mu\text{A}$
Total Capacitance at $V_R = 0, f = 1\text{ MHz}$	$C_T$	40	pF

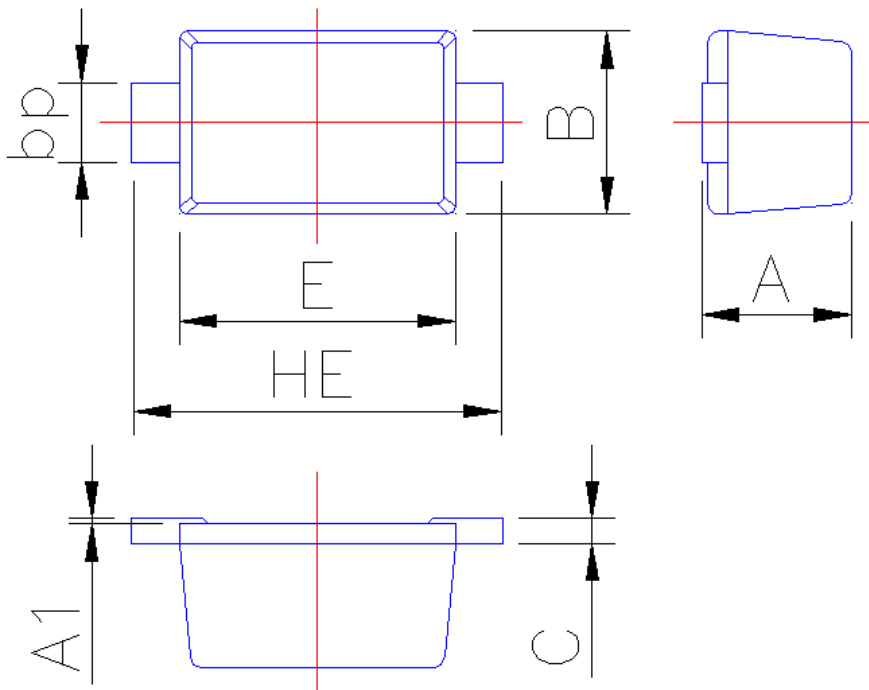




## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70